

## Silicon PNP Epitaxial Planar Type

## 2SA1035

## ■ Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-55	V
Collector-emitter voltage	V <sub>CEO</sub>	-55	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-50	mA
Peak collector current	I <sub>CP</sub>	-100	mA
Collector power dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V <sub>CB0</sub>	I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0	-55			V
Collector-emitter voltage	V <sub>CEO</sub>	I <sub>C</sub> = -2 mA, I <sub>B</sub> = 0	-55			V
Emitter-base voltage	V <sub>EB0</sub>	I <sub>E</sub> = -10 μA, I <sub>C</sub> = 0	-5			V
Base-emitter voltage *	V <sub>BE</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -100 mA		-0.7	-1.0	V
Collector-base cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0			-0.1	μA
Collector-emitter cutoff current	I <sub>CEO</sub>	V <sub>CE</sub> = -10 V, I <sub>B</sub> = 0			-1	μA
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -2 mA	180		700	
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100 mA, I <sub>B</sub> = -10 mA			-0.6	V
Transition frequency	f <sub>T</sub>	V <sub>CB</sub> = -5 V, I <sub>E</sub> = 2 mA, f = 200 MHz		200		MHz
Noise voltage	NV	V <sub>CE</sub> = -10 V, I <sub>C</sub> = -1 mA, G <sub>v</sub> = 80 dB R <sub>g</sub> = 100 kΩ, F <sub>function</sub> = FLAT			150	mV

\* Pulse measurement.

## ■ hFE Classification

Marking	HR	HS	HT
hFE	180~360	260~520	360~700